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Docket No.: 10191/1614

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Inventors : Richard SPITZ et al.
Serial No. : 09/720,720
Filed : February 28, 2001
For : METHOD FOR ELIMINATING DEFECTS IN SILICON
ELEMENTS THROUGH SELECTIVE ETCHING
Examiner : TRAN, Binh
Art Unit : 1765
Confirmation No. : 3872

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Jong H. Lee

RULE 116 AMENDMENT

SIR:

This Amendment addresses the final Office Action mailed March 17, 2003, and it
is respectfully requested that the above-identified application be amended as follows.

In the Claims:

Please amend claims 32 and 34 as shown below:

32. (Amended) A method for etching, comprising:

exposing a silicon element to a first heat treatment in a vacuum at a first elevated
temperature;

selectively etching the silicon element with a gaseous etching medium and forming